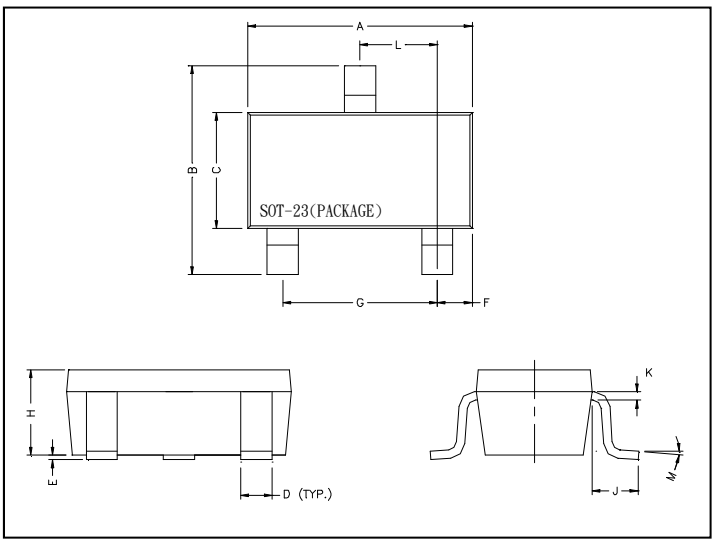
GMBT5087

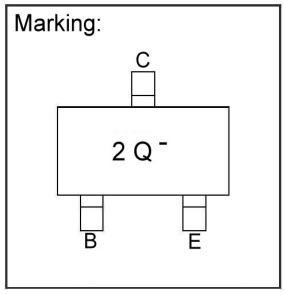
PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT5087 is designed for low noise, high gain and general purpose amplifier applications.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

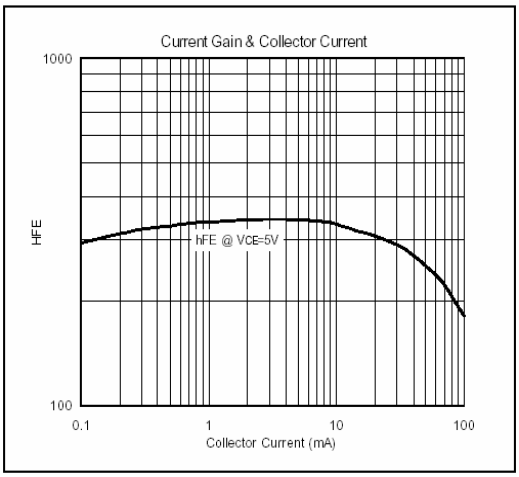
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	VCBO	-50	V
Collector to Emitter Voltage	VCEO	-50	V
Emitter to Base Voltage	VEBO	-3	V
Collector Current	IC	-50	mA
Total Power Dissipation	PD	225	mW

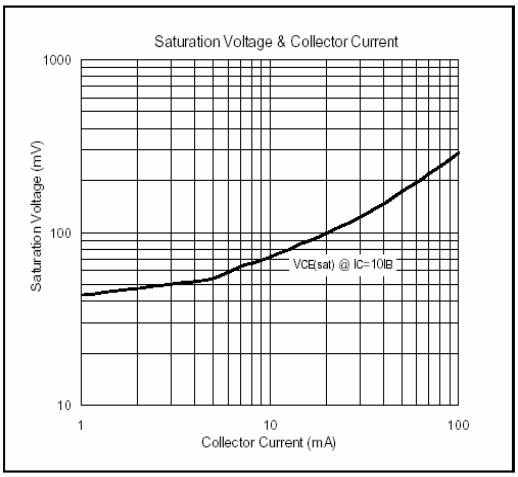
Electrical Characteristics(Ta = 25℃,unless otherwise noted)

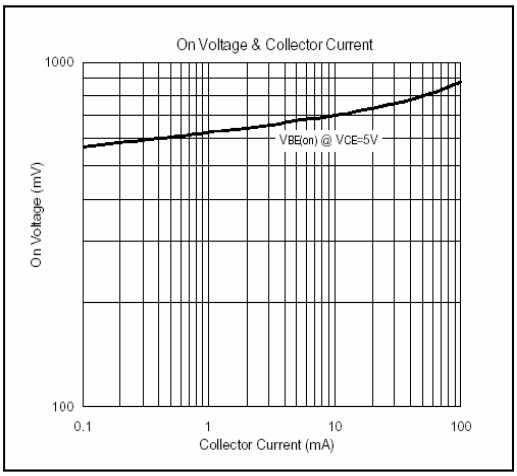
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-50	-	-	V	I_C=-100uA , I_E=0
BV_{CEO}	-50	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-3	-	-	V	I_E=-10uA ,I_C=0
$I_{CBO}1$	-	-	-10	nA	V_{CB}=-10V, I_E=0
$I_{CBO}2$	-	-	-50	nA	V_{CB}=-35V, I_E=0
*$V_{CE(sat)}$	-	-	-300	mV	I_C=-10mA, I_B=-1mA
*$V_{BE(sat)}$	-	-	-850	mV	I_C=-10mA, I_B=-1mA
*$h_{FE}1$	250	-	800		V_{CE}=-5V, I_C=-0.1mA
*$h_{FE}2$	250	-	-		V_{CE}=-5V, I_C=-1mA
*$h_{FE}3$	250	-	-		V_{CE}=-5V, I_C=-10mA
f_T	40	-	-	MHz	V_{CE}=-5V, I_C=-0.5mA, f=100MHz
Cob	-	-	4.0	pF	V_{CB}=-5V, f=100kHz

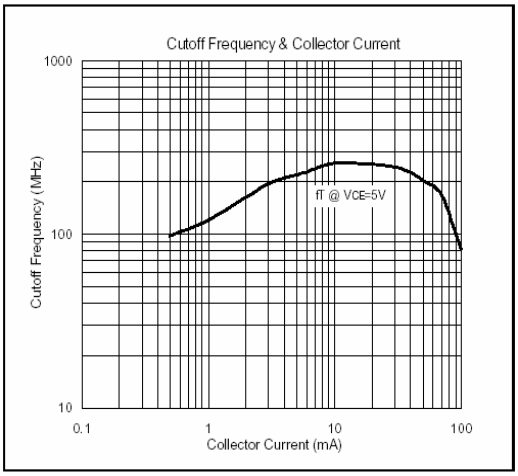
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

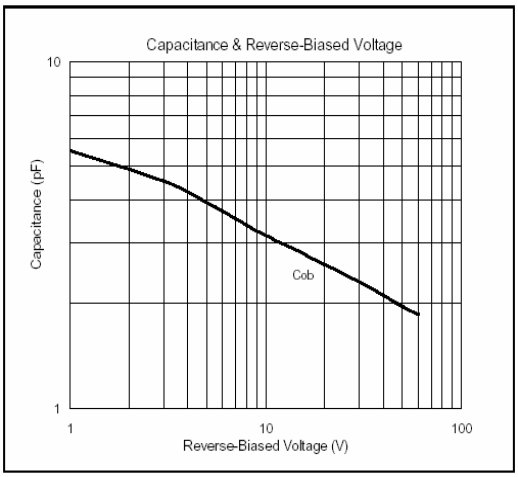
Characteristics Curve

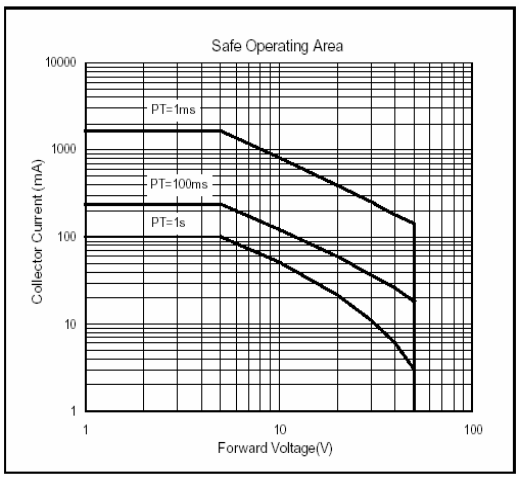












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